

Amendments to the Specification

Please enter the following amendments to the Specification:

On page 1, line 2 please amend the paragraph as follows:

This is a division of Application No. 09/ 296,702, filed October 14, 1999, now ~~allowed~~ U.S. Patent No. 6,358,854.

At the bottom of page 12 and continuing onto page 13, please amend the paragraph as follows:

It is essentially impossible to grow high-quality multi-layered material compositions using a layer-by-layer process when the growth surface has this level of roughness and unevenness. Even in a single layer structure intended for electronic or photonic applications, the scattering and uncontrolled reflections of the carriers from the growth surface will result in poor and somewhat unpredictable performance relative to the design criteria. To solve this problem, and allow general layered material compositions to be grown, Applicants have developed a process to planarize the surface [or] of the structure, and also to reduce its thickness to the proper design value. Chemical-mechanical polishing (CMP) of the growth surface is carried out between deposition of subsequent layers, thereby eliminating the problem. Some of this material was previously disclosed in US Patent ~~Application 09/067,614~~ No. 5,998,298, by inventors including the present inventors, ~~filed on April 28, 1998~~, which is hereby ~~included~~ incorporated by reference.